

SG60N15F

60V N-Channel Power MOSFET

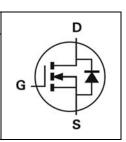
V_{DSS}, 60V

 $R_{DS(ON)}$, $9m\Omega$ (max.) @ $V_{GS}{=}10V$ $R_{DS(ON)}$, $11m\Omega$ (max.) @ $V_{GS}{=}4.5V$

 I_D , 44A



DC-DC converters and Off-line UPS



Description	Features
The SG60N15F uses advanced Trench technology and designs to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	 Low On-Resistance Low Input Capacitance Low Miller Charge Low Input / Output Leakage Pb-free lead plating; RoHS compliant
	Applications
	Motor / Body Load Control Automotive Systems Load Switch

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG60N15F	Halogen-Free	TO-220F	F	Tube	50

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	±20	V
Drain Current-Continuous	T _C =25°C	I-	44	Α
Drain Current-Continuous	T _C =100°C	ID I	28	Α
Drain Current-Pulsed Note 1		I _{DM}	100	А
Avalanche Current		las	35	А
Avalanche Energy, L=0.1mH		E _{AS}	61	mJ
Maximum Davier Dissipation	T _C =25°C	D	31.3	W
Maximum Power Dissipation	T _C =100°C	P _D	12.5	W
Storage Temperature Range		T _{STG}	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	Reja	Steady State	-	-	62	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	4	°C/W

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Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage	Igss	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
ON CHARACTERISTICS	·					
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	$V_{GS(TH)}$	V _{DS} =V _{GS} , I _{DS} =250µA	1.3	1.7	2.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _{DS} =12A	-	-	9	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _{DS} =9A	-	-	11	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss			1486	-	
Output Capacitance	Coss	V _{DS} =30V, V _{GS} =0V, f=1MHz	-	123	-	pF
Reverse Transfer Capacitance	C _{rss}		-/	71	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	14.8	-	
Rise Time	tr	$V_{GS}=10V$, $V_{DS}=30V$, $R_L=5\Omega$,	_	127	-	no
Turn-Off Delay Time	$T_{d(off)}$ R _{GEN} =3 Ω		-	54.2	-	ns
Fall Time	tf		-	75.9	-	
Total Gate Charge	Qg		-	68	-	
Gate to Source Gate Charge	Q_{gs}	V _{GS} =10V, V _{DS} =30V, I _D =12A	-	15.6	-	nC
Gate to Drain "Miller" Charge	Q_{gd}		-	18	-	1
Gate resistance	Rg	V _{DS} =0V, V _{GS} =0V, f=1MHz	-	1.5	-	Ω

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter Symbol Conditions Min. Typ. Max. Unit					Unit	
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =12A	-	-	1.3	V
Continuous Source Current	Is	\/-=\/-=0\/	-	-	52	Α
Pulsed Source Current	Ism	V _G =V _D =0V , Force Current	-	-	120	Α

Notes:

- 1. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- 2. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design. R_{BJA} shown below for single device operation on FR-4 in still air.



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Marking Information

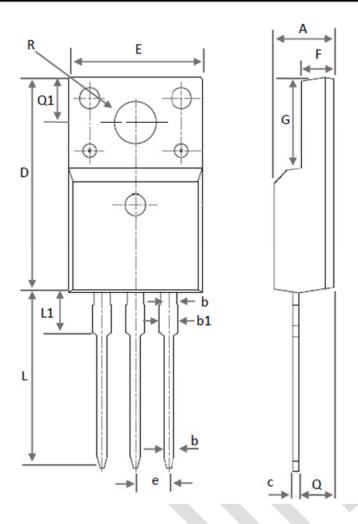
	TO-220F (F)	Marking Rule
Laser Marking		Line 1 : Device
		SG60N15F Line 2: Date Code
	SG60N15F	YYMMXXX
	YYMMXXX	YY: Year Code
		MM: Month Code
		XXX : Serial Number
	Diagram	



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Package of Dimension

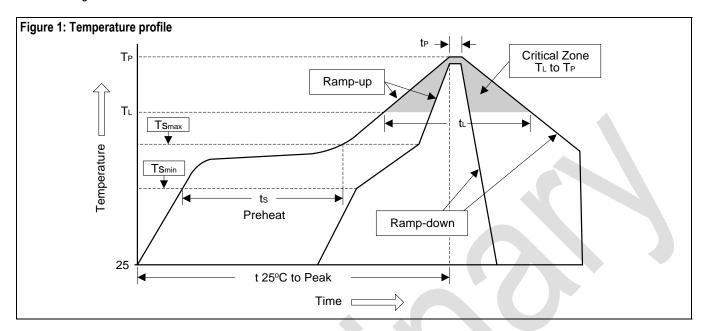


Symbol	Min	Nor	Max
Α	4.50	4.67	4.83
b	0.70	0.81	0.91
b1	1.20	1.34	1.47
b2	1.10	1.24	1.38
C	0.40	0.52	0.63
D	15.67	15.87	16.07
е		2.54 BSC	
Е	9.96	10.16	10.36
F	2.34	2.54	2.74
G	6.48	6.69	6.90
L	12.68	12.99	13.30
L1	3.13	3.32	3.50
Q	2.54	2.74	2.93
Q1	3.20	3.30	3.40
R	3.08	3.18	3.28



Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T _L)	183°C	217°C
- Time (t⊥)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t _P)	10 to 30 sec	20 to 40 Sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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